

BF556A; BF556B; BF556C

N-channel silicon junction field-effect transistors Rev. 4 — 15 September 2011 Prod

Product data sheet

Product profile

1.1 General description

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage.

1.3 Applications

- Impedance converters in e.g. electret microphones and infrared detectors
- VHF amplifiers in oscillators and mixers.

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage (DC)		-	-	±30	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200 \mu A;$ $V_{DS} = 15 V$	-0.5	-	-7.5	V
I _{DSS}	drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
		BF556C	11	-	18	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	-	-	250	mW
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	4.5	-	-	mS



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	source (s)		
2	drain (d)	3	g → s
3	gate (g)	1 7 72	sym054

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BF556A	-	plastic surface mounted package; 3 leads	SOT23			
BF556B						
BF556C						

4. Marking

Table 4. Marking

•	
Type number	Marking code ^[1]
BF556A	24*
BF556B	25*
BF556C	26*

^{[1] * =} p: made in Hong Kong.

^{* =} t: made in Malaysia.

^{* =} W: made in China.

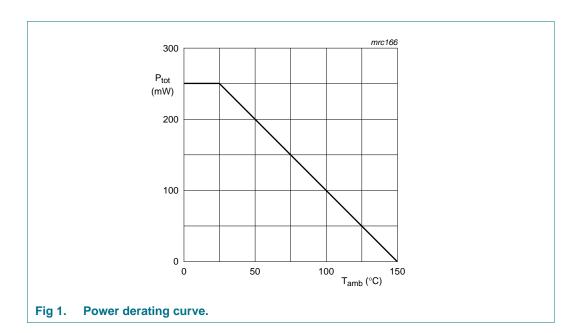
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±30	V
V_{GSO}	gate-source voltage	open drain	-	-30	V
V_{GDO}	gate-drain voltage (DC)	open source	-	-30	V
I _G	forward gate current (DC)		-	10	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> 500	K/W

^[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

7. Static characteristics

Table 7. Static characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G = -1 \mu A$; $V_{DS} = 0 V$	-30	-	-	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200 \ \mu A; \ V_{DS} = 15 \ V$	-0.5	-	-7.5	V
I _{DSS} drain current		$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
		BF556C	11	-	18	mA
I _{GSS}	gate-source leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-0.5	-5000	рΑ
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	4.5	-	-	mS
yos	common source output admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	40	-	μS

8. Dynamic characteristics

Table 8. Dynamic characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V; } f = 1 \text{ MHz}$				
		V _{GS} = −10 V	-	1.7	-	pF
		V _{GS} = 0 V	-	3	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		V _{GS} = −10 V	-	8.0	-	pF
		V _{GS} = 0 V	-	0.9	-	pF
g _{is}	common source input conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
con		f = 100 MHz	-	15	-	μS
		f = 450 MHz	-	300	-	μS
•	common source transfer conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
		f = 100 MHz	-	2	-	mS
		f = 450 MHz	-	1.8	-	mS
g _{rs} c	common source reverse conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$	-	-6	-	μS
		f = 100 MHz	-	-6	-	μS
		f = 450 MHz	-	-40	-	μS
g _{os}	common source output	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	30	-	μS
		f = 450 MHz	-	60	-	μS
V _n	equivalent input noise voltage	$V_{DS} = 10 \text{ V; } I_{D} = 1 \text{ mA;}$ f = 100 Hz	-	40	-	nV/√H

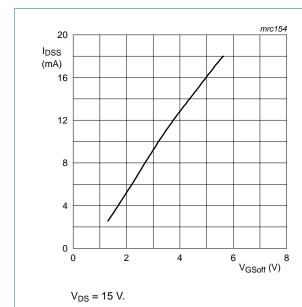
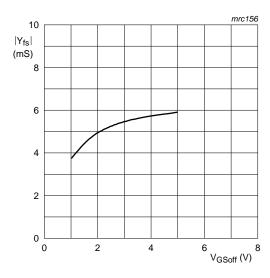


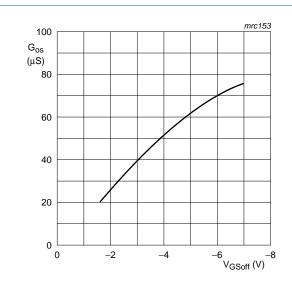
Fig 2. Drain current as a function of gate-source cut-off voltage; typical values.



 $V_{DS} = 15 \text{ V}; I_D = 1 \mu\text{A}.$

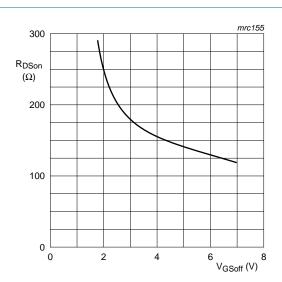
Fig 3. Forward transfer admittance as a function of gate-source cut-off voltage; typical values.

BF556A_BF556B_BF556C



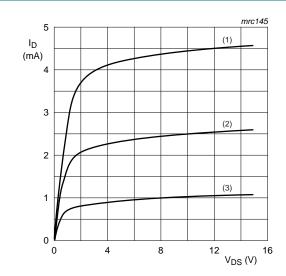
 $V_{DS} = 15 \text{ V}.$

Fig 4. Common-source output conductance as a function of gate-source cut-off voltage; typical values.



 $V_{DS} = 100 \text{ mV}; V_{GS} = 0 \text{ V}.$

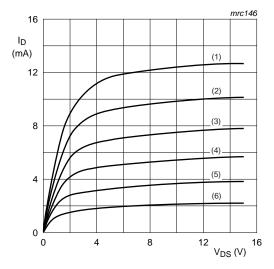
Fig 5. Drain-source on-state resistance as a function of gate-source cut-off voltage; typical values.



BF556A

- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$

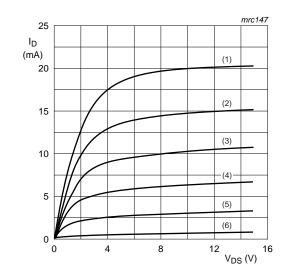
Fig 6. Typical output characteristics.



BF556B

- (1) $V_{GS} = 0 \text{ V}.$
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$
- (4) $V_{GS} = -1.5 \text{ V}.$
- (5) $V_{GS} = -2.0 \text{ V}.$
- (6) $V_{GS} = -2.5 \text{ V}.$

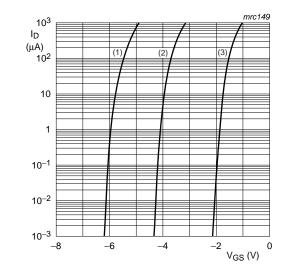
Fig 7. Typical output characteristics.



BF556C

- (1) $V_{GS} = 0 \text{ V}.$
- (2) $V_{GS} = -1.0 \text{ V}.$
- (3) $V_{GS} = -2.0 \text{ V}.$
- (4) $V_{GS} = -3.0 \text{ V}.$
- (5) $V_{GS} = -4.0 \text{ V}.$
- (6) $V_{GS} = -5.0 \text{ V}.$

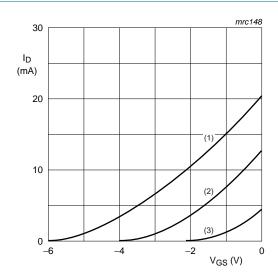
Fig 8. Typical output characteristics.



 $V_{DS} = 15 \text{ V}.$

- (1) BF556C.
- (2) BF556B.
- (3) BF556A.

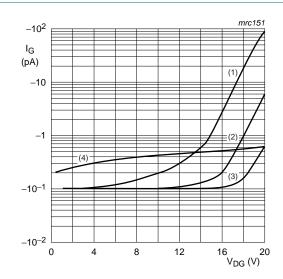
Fig 10. Drain current as a function of gate-source voltage; typical values.



 $V_{DS} = 15 \text{ V}.$

- (1) BF556C.
- (2) BF556B.
- (3) BF556A.

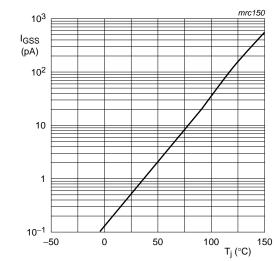
Fig 9. Typical input characteristics.

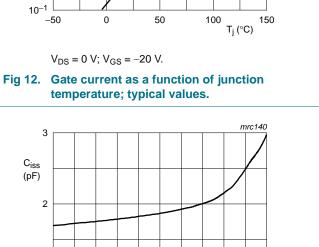


 $I_D = 10$ mA only for BF556B and BF556C.

- (1) $I_D = 10 \text{ mA}.$
- (2) $I_D = 1 \text{ mA}$.
- (3) $I_D = 0.1 \text{ mA}.$
- (4) I_{GSS}.

Fig 11. Gate current as a function of drain-gate voltage; typical values.



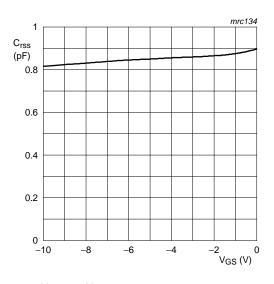


-2_{VGS} (V) 0

 $V_{DS} = 15 \text{ V}.$

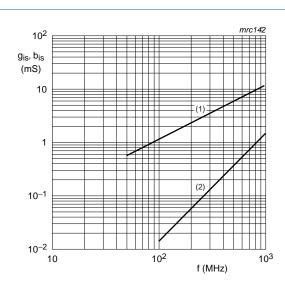
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Fig 14. Input capacitance; typical values.



 $V_{DS} = 15 V.$

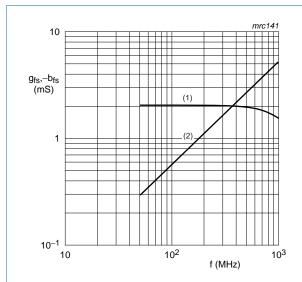
Fig 13. Reverse transfer capacitance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) b_{is}.
- (2) g_{is}.

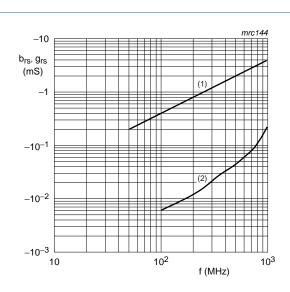
Fig 15. Common-source input admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) g_{fs}
- (2) -b_{fs}.

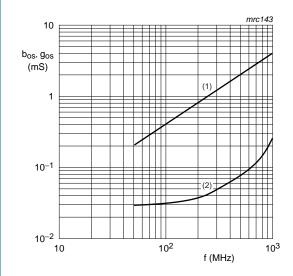
Fig 16. Common-source transfer admittance; typical values.



 $V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}; T_{amb} = 25 \text{ °C}.$

- (1) brs
- (2) g_{rs}.

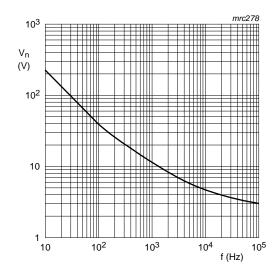
Fig 17. Common-source reverse admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) b_{os}.
- (2) gos.

Fig 18. Common-source output admittance;typical values.



 $V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}.$

Fig 19. Equivalent noise voltage as a function of frequency.

9. Package outline

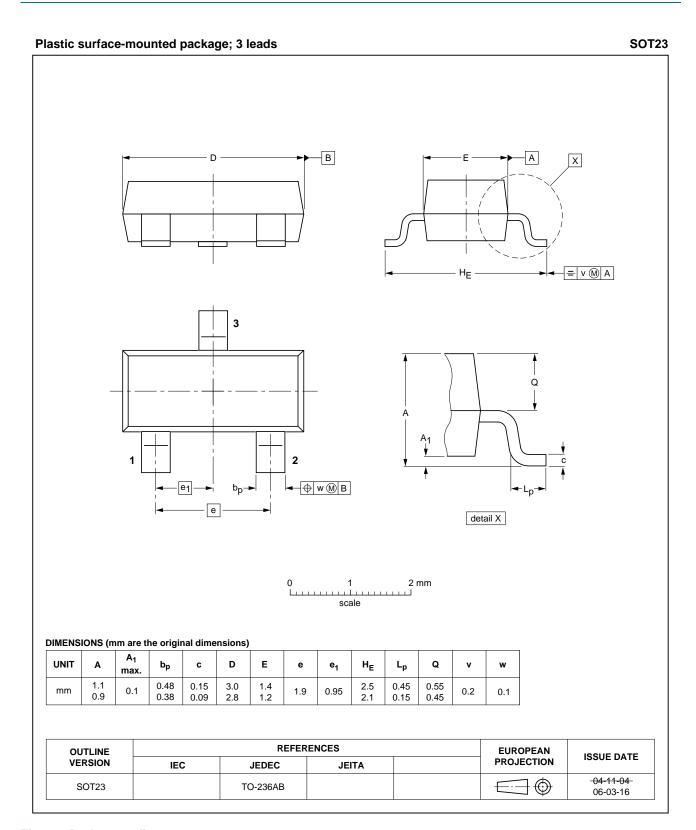


Fig 20. Package outline.

BF556A_BF556B_BF556C

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
			onango nonco	•
BF556A_BF556B_BF556C v.4	20110915	Product data sheet	-	BF556A_BF556B_BF556C v.3
Modifications:		of this data sheet has be of NXP Semiconductors.	•	comply with the new identity
	 Legal texts 	have been adapted to th	ne new company r	name where appropriate.
	 Package ou 	ıtline drawings have bee	n updated to the I	atest version.
BF556A_BF556B_BF556C v.3 (9397 750 13393)	20040805	Product data sheet	-	BF556A-B-C v.2
BF556A-B-C v.2	19960729	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BF556A_BF556B_BF556C

BF556A; BF556B; BF556C

N-channel silicon junction field-effect transistors

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13. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Static characteristics 4
8	Dynamic characteristics 5
9	Package outline
10	Revision history 11
11	Legal information 12
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks
12	Contact information
13	Contents

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